

ABSTRACT

The film acoustic wave devices (12a, 12b and 12c) having the same properties are obtained by changing at least one of the followings: the length and/or the width of upper electrode (18a and 18b); the distance between the upper electrodes (18a and 18b); the length and/or the width of connecting patterns (19a and 19b); areas of bonding pads (20a and 20b); and the pattern shape for the film acoustic wave device (12a and 12b) such as the area of capacitor electrode connected electrically to the bonding pads (20a and 20b); the property variations of film acoustic wave devices (12a, 12b and 12c) caused from the positioning at wafer 11 is compensated.